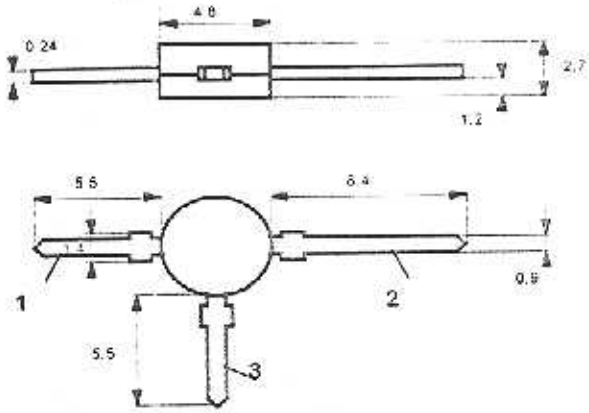
BFW92, BFW92A

Wideband N-P-N bipolar silicon RF transistors



Transistor is designed for application in satellite communication systems, wideband low-noise amplifiers, high-speed switches, HF oscillators. Plastic package SOT-37.

Pinouts:
1- Base, 2- Collector, 3-Emitter

Ratings

Symbol	Parameter, unit	Limits
V_{CB0}	Collector- base voltage, V	20
V_{CE0}	Collector- emitter voltage, V	15
V_{EB0}	Emitter- base voltage, V	2
I_C	Collector current, mA	25
P_{tot}	Power dissipation, mW T_A= -45 to +60°C T_A= +70°C	 280 200

Characteristics (T_A = 25°C)

Symbol	Parameter, unit, test conditions		Limits		
			min	typ	max
f_T	Transition frequency, GHz, I_E=25mA, V_{CB}= 1V I_E=25mA, V_{CB}= 1V	 BFW92 BFW92A	 2.5 3.2		
h_{FE}	DC current gain, I_E=25mA, V_{CB}= 1V I_E=25mA, V_{CB}= 1V	 BFW92 BFW92A	 100 50		
I_{CB0}	Collector cut-off current, nA, V_{CB}=10V				100
G_P	Power gain, dB, I_E=14mA, V_{CE}= 5V, f=800MHz		11		
F	Noise figure, dB, I_E=10mA, V_{CE}= 6V, f=500MHz I_E= 2mA, V_{CB}= 5V, f=800MHz	 BFW92 BFW92A		 2.0 2.5	
C_C	Collector capacitance, pF, V_{CB}=10V, f= 1MHz				0.8

Alternative KT3196D

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